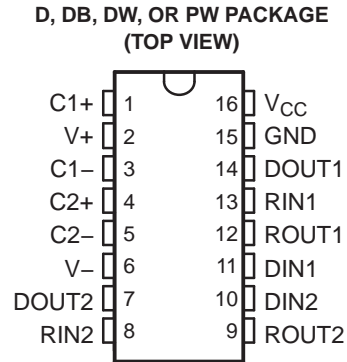


FEATURES

- Operates With 3-V to 5.5-V V_{CC} Supply
- Operates up to 1 Mbit/s
- Low Supply Current . . . 300 μ A Typ
- External Capacitors . . . $4 \times 0.1 \mu$ F
- Accept 5-V Logic Input With 3.3-V Supply
- Latch-Up Performance Exceeds 100 mA Per JESD 78, Class II
- ESD Protection for RS-232 Pins
 - ±15-kV Human-Body Model (HBM)
 - ±15-kV IEC 61000-4-2 Air-Gap Discharge
 - ±8-kV IEC 61000-4-2 Contact Discharge



APPLICATIONS

- Battery-Powered Systems
- PDAs
- Notebooks
- Laptops
- Palmtop PCs
- Hand-Held Equipment

DESCRIPTION/ORDERING INFORMATION

The TRSF3232E consists of two line drivers, two line receivers, and a dual charge-pump circuit with ±15-kV ESD protection pin to pin (serial-port connection pins, including GND). This device provides the electrical interface between an asynchronous communication controller and the serial-port connector. The charge pump and four small external capacitors allow operation from a single 3-V to 5.5-V supply. The TRSF3232E operates at data signaling rates up to 1 Mbit/s and a driver output slew rate of 14 V/ μ s to 150 V/ μ s.

ORDERING INFORMATION

T_A	PACKAGE ⁽¹⁾⁽²⁾		ORDERABLE PART NUMBER	TOP-SIDE MARKING
0°C to 70°C	SOIC – D	Tube of 40	TRSF3232ECD	TRSF3232EC
		Reel of 2500	TRSF3232ECDR	
	SOIC – DW	Tube of 40	TRSF3232ECDW	TRSF3232EC
		Reel of 2000	TRSF3232ECDWR	
	SSOP – DB	Reel of 2000	TRSF3232ECDBR	RT32EC
	TSSOP – PW	Tube of 90	TRSF3232ECPW	RT32EC
Reel of 2000		TRSF3232ECPWR		
–40°C to 85°C	SOIC – D	Tube of 40	TRSF3232EID	TRSF3232EI
		SOIC – DW	TRSF3232EIDR	
	SOIC – DW	Tube of 40	TRSF3232EIDW	TRSF3232EI
		TSSOP – PW	TRSF3232EIDWR	
	SSOP – DB	Reel of 2000	TRSF3232EIDBR	RT32EI
	TSSOP – PW	Tube of 90	TRSF3232EIPW	RT32EI
		Reel of 2000	TRSF3232EIPWR	

(1) Package drawings, thermal data, and symbolization are available at www.ti.com/packaging.

(2) For the most current package and ordering information, see the Package Option Addendum at the end of this document, or see the TI website at www.ti.com.



Please be aware that an important notice concerning availability, standard warranty, and use in critical applications of Texas Instruments semiconductor products and disclaimers thereto appears at the end of this data sheet.

TRSF3232E
3-V TO 5.5-V TWO-CHANNEL RS-232 1-Mbit/s LINE DRIVER/RECEIVER
WITH ± 15 -kV IEC ESD PROTECTION

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Table 1. 1-Mbit/s RS-232 Parts

TEMPERATURE RANGE	PART NO.	NO. OF DRIVERS	NO. OF RECEIVERS	ESD	SUPPLY V_{CC} (V)	FEATURE	PIN/PACKAGE
0°C to 70°C	TRSF3221E	1	1	± 15 -kV Air-Gap Discharge, ± 8 -kV Contact Discharge, ± 15 -kV HBM	3.3 or 5	Auto-powerdown	16-pin SOIC, SSOP, TSSOP
	TRSF3232E	2	2	± 15 -kV Air-Gap Discharge, ± 8 -kV Contact Discharge, ± 15 -kV HBM	3.3 or 5	Low pin count	16-pin SOIC, SSOP, TSSOP
	TRS3227	1	1	± 8 -kV Air-Gap Discharge, ± 8 -kV Contact Discharge, ± 15 -kV HBM	3.3 or 5	Auto-powerdown plus, ready signal	16-pin SSOP
	TRSF3221	1	1	± 15 -kV HBM	3.3 or 5	Auto-powerdown	16-pin SOIC, SSOP, TSSOP
	TRSF3222	2	2	± 15 -kV HBM	3.3 or 5	Enable, powerdown signal	20-pin SOIC, SSOP, TSSOP
	TRSF3223	2	2	± 15 -kV HBM	3.5 or 5	Auto-powerdown, enable signal	20-pin SOIC, SSOP, TSSOP
	TRSF3232	2	2	± 15 -kV HBM	3.3 or 5	Low pin count	16-pin SOIC, SSOP, TSSOP
	TRSF3238	5	3	± 15 -kV HBM	3.3 or 5	Auto-powerdown plus	28-pin SOIC, SSOP, TSSOP
	TRSF3243	3	5	± 15 -kV HBM	3.3 or 5	Auto-powerdown	28-pin SOIC, SSOP, TSSOP
–40°C to 85°C	TRSF3221E	1	1	± 15 -kV Air-Gap Discharge, ± 8 -kV Contact Discharge, ± 15 -kV HBM	3.3 or 5	Auto-powerdown	16-pin SOIC, SSOP, TSSOP
	TRSF3232E	2	2	± 15 -kV Air-Gap Discharge, ± 8 -kV Contact Discharge, ± 15 -kV HBM	3.3 or 5	Low pin count	16-pin SOIC, SSOP, TSSOP
	TRS3227	1	1	± 8 -kV Air-Gap Discharge, ± 8 -kV Contact Discharge, ± 15 -kV HBM	3.3 or 5	Auto-powerdown plus, ready signal	16-pin SSOP
	TRSF3221	1	1	± 15 -kV HBM	3.3 or 5	Auto-powerdown	16-pin SOIC, SSOP, TSSOP
	TRSF3222	2	2	± 15 -kV HBM	3.3 or 5	Enable, powerdown signal	20-pin SOIC, SSOP, TSSOP
	TRSF3223	2	2	± 15 -kV HBM	3.3 or 5	Auto-powerdown, enable signal	20-pin SOIC, SSOP, TSSOP
	TRSF3232	2	2	± 15 -kV HBM	3.3 or 5	Low pin count	16-pin SOIC, SSOP, TSSOP
	TRSF3238	5	3	± 15 -kV HBM	3.3 or 5	Auto-powerdown plus	28-pin SOIC, SSOP, TSSOP
	TRSF3243	3	5	± 15 -kV HBM	3.3 or 5	Auto-powerdown	28-pin SOIC, SSOP, TSSOP

FUNCTION TABLES

Each Driver⁽¹⁾

INPUT DIN	OUTPUT DOUT
L	H
H	L

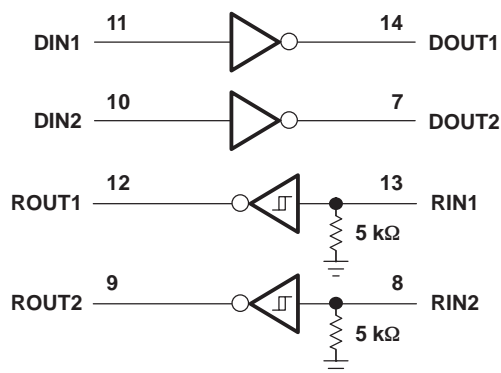
(1) H = high level, L = low level

Each Receiver⁽¹⁾

INPUT RIN	OUTPUT ROUT
L	H
H	L
Open	H

(1) H = high level, L = low level,
Open = input disconnected or
connected driver off

LOGIC DIAGRAM (POSITIVE LOGIC)



TRSF3232E
3-V TO 5.5-V TWO-CHANNEL RS-232 1-Mbit/s LINE DRIVER/RECEIVER
WITH ± 15 -kV IEC ESD PROTECTION

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Absolute Maximum Ratings⁽¹⁾

over operating free-air temperature range (unless otherwise noted)

		MIN	MAX	UNIT	
V_{CC}	Supply voltage range ⁽²⁾	-0.3	6	V	
V+	Positive-output supply voltage range ⁽²⁾	-0.3	7	V	
V-	Negative-output supply voltage range ⁽²⁾	0.3	-7	V	
V+ - V-	Supply voltage difference ⁽²⁾		13	V	
V_I	Input voltage range	Drivers	-0.3	6	V
		Receivers	-25	25	
V_O	Output voltage range	Drivers	-13.2	13.2	V
		Receivers	-0.3	$V_{CC} + 0.3$	
θ_{JA}	Package thermal impedance ⁽³⁾⁽⁴⁾	D package		82	°C/W
		DB package		46	
		DW package		57	
		PW package		108	
T_J	Operating virtual junction temperature		150	°C	
T_{stg}	Storage temperature range	-65	150	°C	

- (1) Stresses beyond those listed under "absolute maximum ratings" may cause permanent damage to the device. These are stress ratings only, and functional operation of the device at these or any other conditions beyond those indicated under "recommended operating conditions" is not implied. Exposure to absolute-maximum-rated conditions for extended periods may affect device reliability.
- (2) All voltages are with respect to network GND.
- (3) Maximum power dissipation is a function of $T_J(\text{max})$, θ_{JA} , and T_A . The maximum allowable power dissipation at any allowable ambient temperature is $P_D = (T_J(\text{max}) - T_A)/\theta_{JA}$. Operating at the absolute maximum T_J of 150°C can affect reliability.
- (4) The package thermal impedance is calculated in accordance with JESD 51-7.

Recommended Operating Conditions⁽¹⁾

		MIN	NOM	MAX	UNIT	
Supply voltage		$V_{CC} = 3.3\text{ V}$	3	3.3	3.6	V
		$V_{CC} = 5\text{ V}$	4.5	5	5.5	
V_{IH}	Driver high-level input voltage	DIN	$V_{CC} = 3.3\text{ V}$	2		V
			$V_{CC} = 5\text{ V}$	2.4		
V_{IL}	Driver low-level input voltage	DIN		0.8	V	
V_I	Driver input voltage	DIN	0	5.5	V	
	Receiver input voltage		-25	25		
T_A	Operating free-air temperature	TRSF3232EI	-40	85	°C	
		TRSF3232EC	0	70		

- (1) Test conditions are C1–C4 = 0.1 μF at $V_{CC} = 3.3\text{ V} \pm 0.3\text{ V}$; C1 = 0.047 μF , C2–C4 = 0.33 μF at $V_{CC} = 5\text{ V} \pm 0.5\text{ V}$ (see Figure 4).

Electrical Characteristics⁽¹⁾

over recommended ranges of supply voltage and operating free-air temperature (unless otherwise noted)

PARAMETER	TEST CONDITIONS	MIN	TYP ⁽²⁾	MAX	UNIT
I_{CC}	Supply current	No load, $V_{CC} = 3.3\text{ V}$ or 5 V	0.3	1	mA

- (1) Test conditions are C1–C4 = 0.1 μF at $V_{CC} = 3.3\text{ V} \pm 0.3\text{ V}$; C1 = 0.047 μF , C2–C4 = 0.33 μF at $V_{CC} = 5\text{ V} \pm 0.5\text{ V}$ (see Figure 4).
- (2) All typical values are at $V_{CC} = 3.3\text{ V}$ or $V_{CC} = 5\text{ V}$, and $T_A = 25^\circ\text{C}$.

DRIVER SECTION

Electrical Characteristics⁽¹⁾

over recommended ranges of supply voltage and operating free-air temperature (unless otherwise noted)

PARAMETER	TEST CONDITIONS	MIN	TYP ⁽²⁾	MAX	UNIT
V _{OH} High-level output voltage	DOUT at R _L = 3 k Ω to GND, DIN = GND	5	5.5		V
V _{OL} Low-level output voltage	DOUT at R _L = 3 k Ω to GND, DIN = V _{CC}	–5	–5.4		V
I _{IH} High-level input current	V _I = V _{CC}		± 0.01	± 1	μ A
I _{IL} Low-level input current	V _I at GND		± 0.01	± 1	μ A
I _{OS} ⁽³⁾ Short-circuit output current	V _{CC} = 3.6 V, V _O = 0 V		± 35	± 60	mA
	V _{CC} = 5.5 V, V _O = 0 V		± 35	± 90	
r _o Output resistance	V _{CC} , V ₊ , and V _– = 0 V, V _O = ± 2 V	300	10M		Ω

(1) Test conditions are C1–C4 = 0.1 μ F at V_{CC} = 3.3 V \pm 0.3 V; C1 = 0.047 μ F, C2–C4 = 0.33 μ F at V_{CC} = 5 V \pm 0.5 V (see Figure 4).

(2) All typical values are at V_{CC} = 3.3 V or V_{CC} = 5 V, and T_A = 25°C.

(3) Short-circuit durations should be controlled to prevent exceeding the device absolute power dissipation ratings, and not more than one output should be shorted at a time.

Switching Characteristics⁽¹⁾

over recommended ranges of supply voltage and operating free-air temperature (unless otherwise noted)

PARAMETER	TEST CONDITIONS	MIN	TYP ⁽²⁾	MAX	UNIT
Maximum data rate (see Figure 1)	R _L = 3 k Ω , One DOUT switching	C _L = 250 pF, V _{CC} = 3 V to 4.5 V	1000		kbit/s
		C _L = 1000 pF, V _{CC} = 3.5 V to 5.5 V	1000		
t _{sk(p)} Pulse skew ⁽³⁾	C _L = 150 pF to 2500 pF, R _L = 3 k Ω to 7 k Ω , See Figure 2		300		ns
SR(tr) Slew rate, transition region (see Figure 1)	R _L = 3 k Ω to 7 k Ω , C _L = 150 pF to 1000 pF, V _{CC} = 3.3 V		14	150	V/ μ s

(1) Test conditions are C1–C4 = 0.1 μ F at V_{CC} = 3.3 V \pm 0.3 V; C1 = 0.047 μ F, C2–C4 = 0.33 μ F at V_{CC} = 5 V \pm 0.5 V (see Figure 4).

(2) All typical values are at V_{CC} = 3.3 V or V_{CC} = 5 V, and T_A = 25°C.

(3) Pulse skew is defined as |t_{PLH} – t_{PHL}| of each channel of the same device.

ESD Protection

TERMINAL		TEST CONDITIONS	TYP	UNIT
NAME	NO.			
DOUT	7, 14	HBM	± 15	kV
		IEC 61000-4-2 Air-Gap Discharge	± 15	
		IEC 61000-4-2 Contact Discharge	± 8	

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WITH ±15-kV IEC ESD PROTECTION

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RECEIVER SECTION

Electrical Characteristics⁽¹⁾

over recommended ranges of supply voltage and operating free-air temperature (unless otherwise noted)

PARAMETER		TEST CONDITIONS	MIN	TYP ⁽²⁾	MAX	UNIT
V _{OH}	High-level output voltage	I _{OH} = -1 mA	V _{CC} - 0.6	V _{CC} - 0.1		V
V _{OL}	Low-level output voltage	I _{OL} = 1.6 mA			0.4	V
V _{IT+}	Positive-going input threshold voltage	V _{CC} = 3.3 V		1.5	2.4	V
		V _{CC} = 5 V		1.8	2.4	
V _{IT-}	Negative-going input threshold voltage	V _{CC} = 3.3 V	0.6	1.2		V
		V _{CC} = 5 V	0.8	1.5		
V _{hys}	Input hysteresis (V _{IT+} - V _{IT-})			0.3		V
r _i	Input resistance	V _i = ±3 V to ±25 V	3	5	7	kΩ

(1) Test conditions are C1–C4 = 0.1 μF at V_{CC} = 3.3 V ± 0.3 V; C1 = 0.047 μF, C2–C4 = 0.33 μF at V_{CC} = 5 V ± 0.5 V (see Figure 4).

(2) All typical values are at V_{CC} = 3.3 V or V_{CC} = 5 V, and T_A = 25°C.

Switching Characteristics⁽¹⁾

over recommended ranges of supply voltage and operating free-air temperature (unless otherwise noted)

PARAMETER		TEST CONDITIONS	TYP ⁽²⁾	UNIT
t _{PLH}	Propagation delay time, low- to high-level output	C _L = 150 pF	300	ns
t _{PHL}	Propagation delay time, high- to low-level output	C _L = 150 pF	300	ns
t _{sk(p)}	Pulse skew ⁽³⁾		300	ns

(1) Test conditions are C1–C4 = 0.1 μF at V_{CC} = 3.3 V ± 0.3 V; C1 = 0.047 μF, C2–C4 = 0.33 μF at V_{CC} = 5 V ± 0.5 V (see Figure 4).

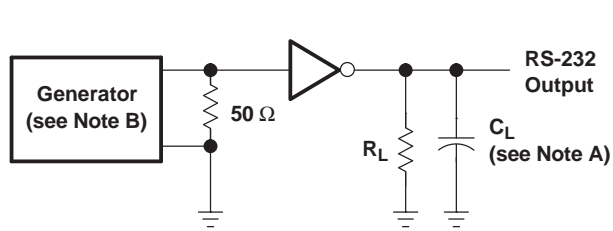
(2) All typical values are at V_{CC} = 3.3 V or V_{CC} = 5 V, and T_A = 25°C.

(3) Pulse skew is defined as |t_{PLH} - t_{PHL}| of each channel of the same device.

ESD Protection

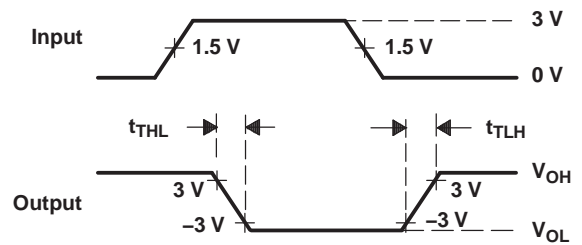
TERMINAL		TEST CONDITIONS	TYP	UNIT
NAME	NO.			
RIN	8, 13	HBM	±15	kV
		IEC 61000-4-2 Air-Gap Discharge	±15	
		IEC 61000-4-2 Contact Discharge	±8	

PARAMETER MEASUREMENT INFORMATION



TEST CIRCUIT

$$SR(tr) = \frac{6\text{ V}}{t_{THL} \text{ or } t_{TLH}}$$

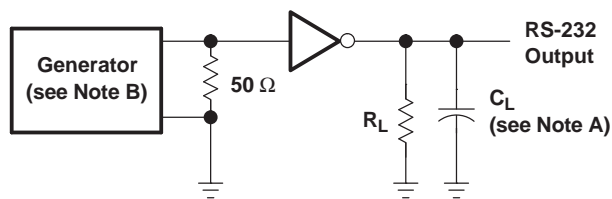


VOLTAGE WAVEFORMS

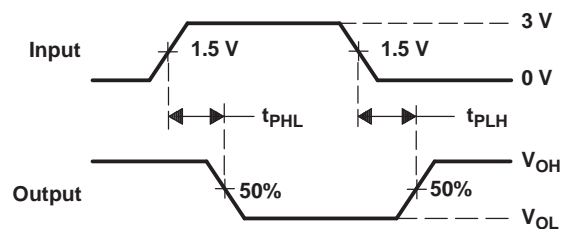
NOTES: A. C_L includes probe and jig capacitance.

B. The pulse generator has the following characteristics: PRR = 250 kbit/s, $Z_O = 50\ \Omega$, 50% duty cycle, $t_r \leq 10\text{ ns}$, $t_f \leq 10\text{ ns}$.

Figure 1. Driver Slew Rate



TEST CIRCUIT

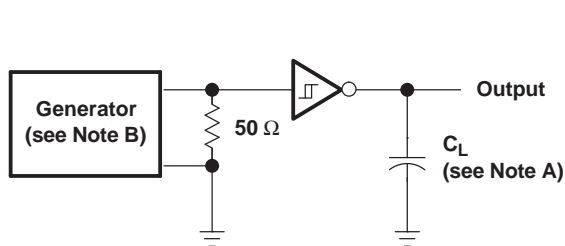


VOLTAGE WAVEFORMS

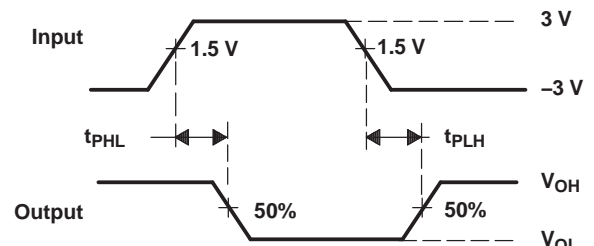
NOTES: A. C_L includes probe and jig capacitance.

B. The pulse generator has the following characteristics: PRR = 250 kbit/s, $Z_O = 50\ \Omega$, 50% duty cycle, $t_r \leq 10\text{ ns}$, $t_f \leq 10\text{ ns}$.

Figure 2. Driver Pulse Skew



TEST CIRCUIT



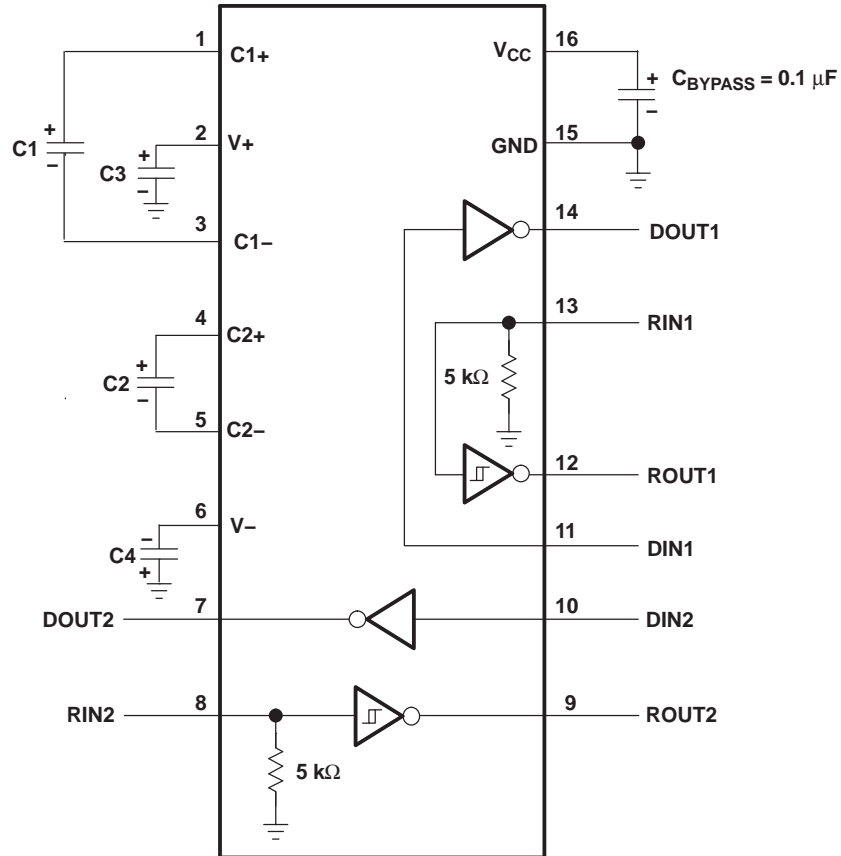
VOLTAGE WAVEFORMS

NOTES: A. C_L includes probe and jig capacitance.

B. The pulse generator has the following characteristics: $Z_O = 50\ \Omega$, 50% duty cycle, $t_r \leq 10\text{ ns}$, $t_f \leq 10\text{ ns}$.

Figure 3. Receiver Propagation Delay Times

APPLICATION INFORMATION



V_{CC} vs CAPACITOR VALUES

V _{CC}	C1	C2, C3, C4
3.3 V ± 0.3 V	0.1 μF	0.1 μF
5 V ± 0.5 V	0.047 μF	0.33 μF
3 V to 5.5 V	0.1 μF	0.47 μF

A. C3 can be connected to V_{CC} or GND.

Figure 4. Typical Operating Circuit and Capacitor Values

PACKAGING INFORMATION

Orderable Device	Status (1)	Package Type	Package Drawing	Pins	Package Qty	Eco Plan (2)	Lead/Ball Finish (6)	MSL Peak Temp (3)	Op Temp (°C)	Device Marking (4/5)	Samples
TRSF3232ECD	ACTIVE	SOIC	D	16	40	Green (RoHS & no Sb/Br)	CU NIPDAU	Level-1-260C-UNLIM	0 to 70	TRSF3232EC	Samples
TRSF3232ECDB	ACTIVE	SSOP	DB	16	80	Green (RoHS & no Sb/Br)	CU NIPDAU	Level-1-260C-UNLIM	0 to 70	RT32EC	Samples
TRSF3232ECDBR	ACTIVE	SSOP	DB	16	2000	Green (RoHS & no Sb/Br)	CU NIPDAU	Level-1-260C-UNLIM	0 to 70	RT32EC	Samples
TRSF3232ECDBRG4	ACTIVE	SSOP	DB	16	2000	Green (RoHS & no Sb/Br)	CU NIPDAU	Level-1-260C-UNLIM	0 to 70	RT32EC	Samples
TRSF3232ECDR	ACTIVE	SOIC	D	16	2500	Green (RoHS & no Sb/Br)	CU NIPDAU	Level-1-260C-UNLIM	0 to 70	TRSF3232EC	Samples
TRSF3232ECDWR	ACTIVE	SOIC	DW	16	2000	Green (RoHS & no Sb/Br)	CU NIPDAU	Level-1-260C-UNLIM	0 to 70	TRSF3232EC	Samples
TRSF3232ECPWR	ACTIVE	TSSOP	PW	16	2000	Green (RoHS & no Sb/Br)	CU NIPDAU	Level-1-260C-UNLIM	0 to 70	RT32EC	Samples
TRSF3232EID	ACTIVE	SOIC	D	16	40	Green (RoHS & no Sb/Br)	CU NIPDAU	Level-1-260C-UNLIM	-40 to 85	TRSF3232EI	Samples
TRSF3232EIDBR	ACTIVE	SSOP	DB	16	2000	Green (RoHS & no Sb/Br)	CU NIPDAU	Level-1-260C-UNLIM	-40 to 85	RT32EI	Samples
TRSF3232EIDR	ACTIVE	SOIC	D	16	2500	Green (RoHS & no Sb/Br)	CU NIPDAU	Level-1-260C-UNLIM	-40 to 85	TRSF3232EI	Samples
TRSF3232EIDW	ACTIVE	SOIC	DW	16	40	Green (RoHS & no Sb/Br)	CU NIPDAU	Level-1-260C-UNLIM	-40 to 85	TRSF3232EI	Samples
TRSF3232EIDWR	ACTIVE	SOIC	DW	16	2000	Green (RoHS & no Sb/Br)	CU NIPDAU	Level-1-260C-UNLIM	-40 to 85	TRSF3232EI	Samples
TRSF3232EIPW	ACTIVE	TSSOP	PW	16	90	Green (RoHS & no Sb/Br)	CU NIPDAU	Level-1-260C-UNLIM	-40 to 85	RT32EI	Samples
TRSF3232EIPWR	ACTIVE	TSSOP	PW	16	2000	Green (RoHS & no Sb/Br)	CU NIPDAU	Level-1-260C-UNLIM	-40 to 85	RT32EI	Samples

(1) The marketing status values are defined as follows:

ACTIVE: Product device recommended for new designs.

LIFEBUY: TI has announced that the device will be discontinued, and a lifetime-buy period is in effect.

NRND: Not recommended for new designs. Device is in production to support existing customers, but TI does not recommend using this part in a new design.

PREVIEW: Device has been announced but is not in production. Samples may or may not be available.

OBSOLETE: TI has discontinued the production of the device.

⁽²⁾ **RoHS:** TI defines "RoHS" to mean semiconductor products that are compliant with the current EU RoHS requirements for all 10 RoHS substances, including the requirement that RoHS substance do not exceed 0.1% by weight in homogeneous materials. Where designed to be soldered at high temperatures, "RoHS" products are suitable for use in specified lead-free processes. TI may reference these types of products as "Pb-Free".

RoHS Exempt: TI defines "RoHS Exempt" to mean products that contain lead but are compliant with EU RoHS pursuant to a specific EU RoHS exemption.

Green: TI defines "Green" to mean the content of Chlorine (Cl) and Bromine (Br) based flame retardants meet JS709B low halogen requirements of ≤ 1000 ppm threshold. Antimony trioxide based flame retardants must also meet the ≤ 1000 ppm threshold requirement.

⁽³⁾ MSL, Peak Temp. - The Moisture Sensitivity Level rating according to the JEDEC industry standard classifications, and peak solder temperature.

⁽⁴⁾ There may be additional marking, which relates to the logo, the lot trace code information, or the environmental category on the device.

⁽⁵⁾ Multiple Device Markings will be inside parentheses. Only one Device Marking contained in parentheses and separated by a "-" will appear on a device. If a line is indented then it is a continuation of the previous line and the two combined represent the entire Device Marking for that device.

⁽⁶⁾ Lead/Ball Finish - Orderable Devices may have multiple material finish options. Finish options are separated by a vertical ruled line. Lead/Ball Finish values may wrap to two lines if the finish value exceeds the maximum column width.

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TAPE AND REEL INFORMATION



QUADRANT ASSIGNMENTS FOR PIN 1 ORIENTATION IN TAPE



*All dimensions are nominal

Device	Package Type	Package Drawing	Pins	SPQ	Reel Diameter (mm)	Reel Width W1 (mm)	A0 (mm)	B0 (mm)	K0 (mm)	P1 (mm)	W (mm)	Pin1 Quadrant
TRSF3232ECDR	SOIC	D	16	2500	330.0	16.4	6.5	10.3	2.1	8.0	16.0	Q1
TRSF3232ECDWR	SOIC	DW	16	2000	330.0	16.4	10.75	10.7	2.7	12.0	16.0	Q1
TRSF3232ECPWR	TSSOP	PW	16	2000	330.0	12.4	6.9	5.6	1.6	8.0	12.0	Q1
TRSF3232EIDR	SOIC	D	16	2500	330.0	16.4	6.5	10.3	2.1	8.0	16.0	Q1
TRSF3232EIDWR	SOIC	DW	16	2000	330.0	16.4	10.75	10.7	2.7	12.0	16.0	Q1
TRSF3232EIPWR	TSSOP	PW	16	2000	330.0	12.4	6.9	5.6	1.6	8.0	12.0	Q1

TAPE AND REEL BOX DIMENSIONS



*All dimensions are nominal

Device	Package Type	Package Drawing	Pins	SPQ	Length (mm)	Width (mm)	Height (mm)
TRSF3232ECDR	SOIC	D	16	2500	367.0	367.0	38.0
TRSF3232ECDWR	SOIC	DW	16	2000	350.0	350.0	43.0
TRSF3232ECPWR	TSSOP	PW	16	2000	367.0	367.0	35.0
TRSF3232EIDR	SOIC	D	16	2500	367.0	367.0	38.0
TRSF3232EIDWR	SOIC	DW	16	2000	350.0	350.0	43.0
TRSF3232EIPWR	TSSOP	PW	16	2000	367.0	367.0	35.0



4220204/A 02/2017

NOTES:

1. All linear dimensions are in millimeters. Any dimensions in parenthesis are for reference only. Dimensioning and tolerancing per ASME Y14.5M.
2. This drawing is subject to change without notice.
3. This dimension does not include mold flash, protrusions, or gate burrs. Mold flash, protrusions, or gate burrs shall not exceed 0.15 mm per side.
4. This dimension does not include interlead flash. Interlead flash shall not exceed 0.25 mm per side.
5. Reference JEDEC registration MO-153.

EXAMPLE BOARD LAYOUT

PW0016A

TSSOP - 1.2 mm max height

SMALL OUTLINE PACKAGE



LAND PATTERN EXAMPLE
EXPOSED METAL SHOWN
SCALE: 10X



4220204/A 02/2017

NOTES: (continued)

- 6. Publication IPC-7351 may have alternate designs.
- 7. Solder mask tolerances between and around signal pads can vary based on board fabrication site.

EXAMPLE STENCIL DESIGN

PW0016A

TSSOP - 1.2 mm max height

SMALL OUTLINE PACKAGE



SOLDER PASTE EXAMPLE
BASED ON 0.125 mm THICK STENCIL
SCALE: 10X

4220204/A 02/2017

NOTES: (continued)

8. Laser cutting apertures with trapezoidal walls and rounded corners may offer better paste release. IPC-7525 may have alternate design recommendations.
9. Board assembly site may have different recommendations for stencil design.

GENERIC PACKAGE VIEW

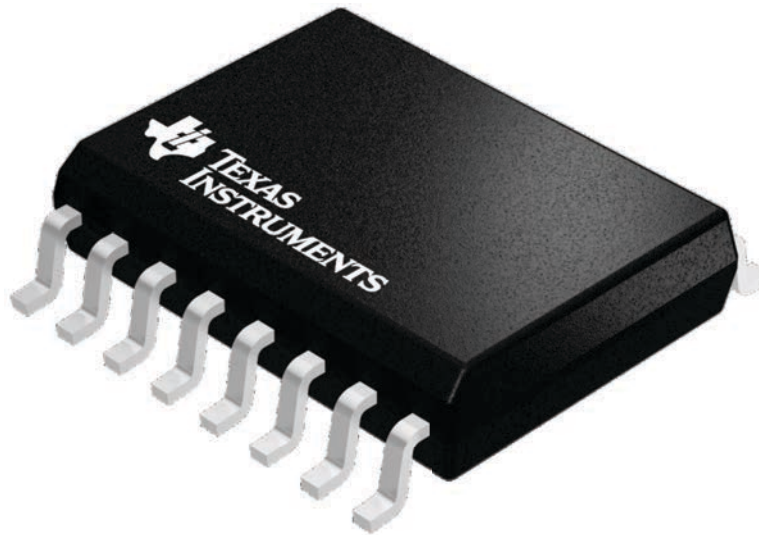
DW 16

SOIC - 2.65 mm max height

7.5 x 10.3, 1.27 mm pitch

SMALL OUTLINE INTEGRATED CIRCUIT

This image is a representation of the package family, actual package may vary.
Refer to the product data sheet for package details.



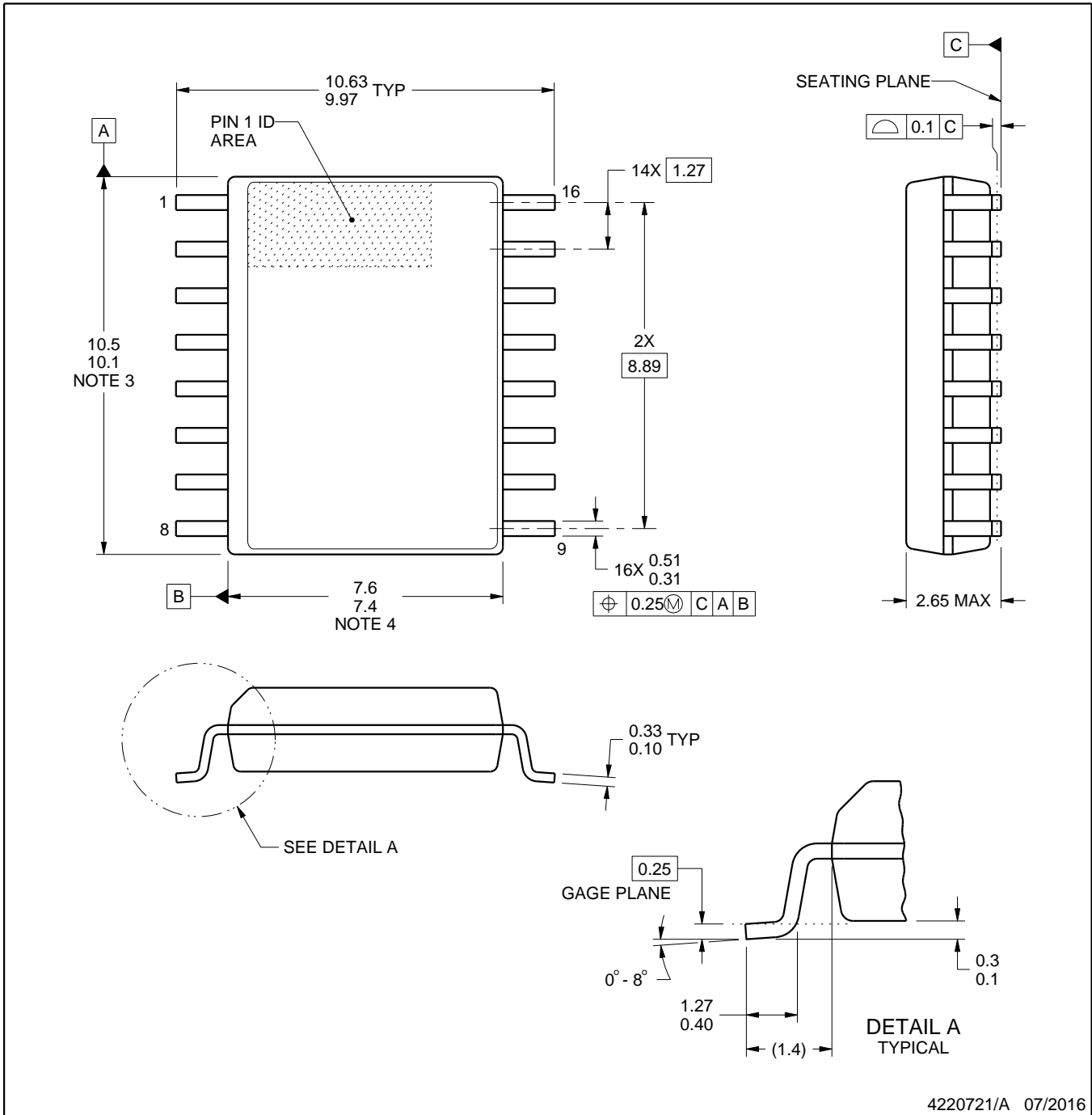
4224780/A



DW0016A

PACKAGE OUTLINE SOIC - 2.65 mm max height

SOIC



4220721/A 07/2016

NOTES:

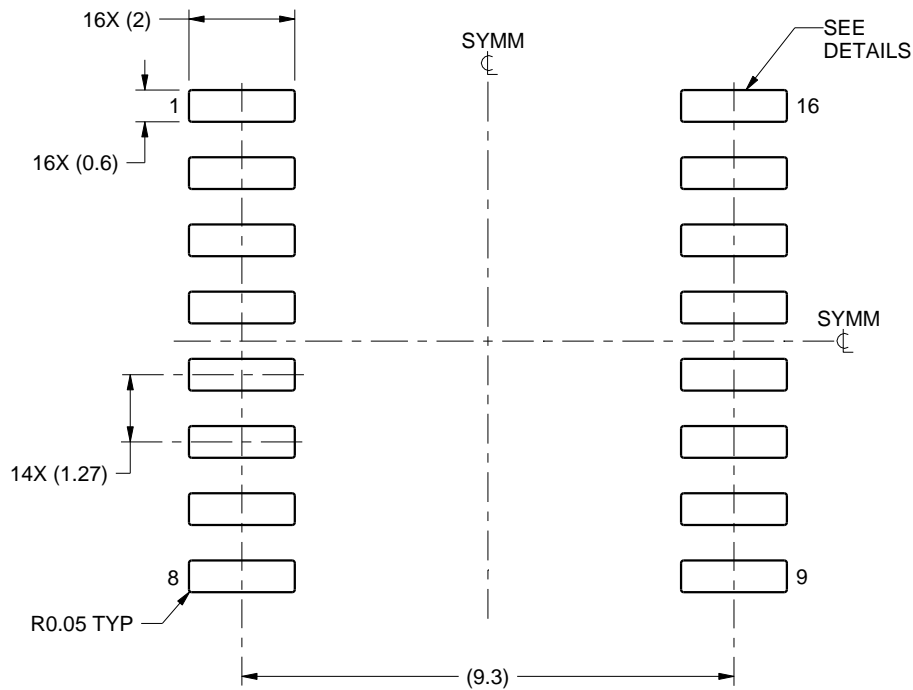
1. All linear dimensions are in millimeters. Dimensions in parenthesis are for reference only. Dimensioning and tolerancing per ASME Y14.5M.
2. This drawing is subject to change without notice.
3. This dimension does not include mold flash, protrusions, or gate burrs. Mold flash, protrusions, or gate burrs shall not exceed 0.15 mm, per side.
4. This dimension does not include interlead flash. Interlead flash shall not exceed 0.25 mm, per side.
5. Reference JEDEC registration MS-013.

EXAMPLE BOARD LAYOUT

DW0016A

SOIC - 2.65 mm max height

SOIC



LAND PATTERN EXAMPLE
SCALE:7X



SOLDER MASK DETAILS

4220721/A 07/2016

NOTES: (continued)

6. Publication IPC-7351 may have alternate designs.

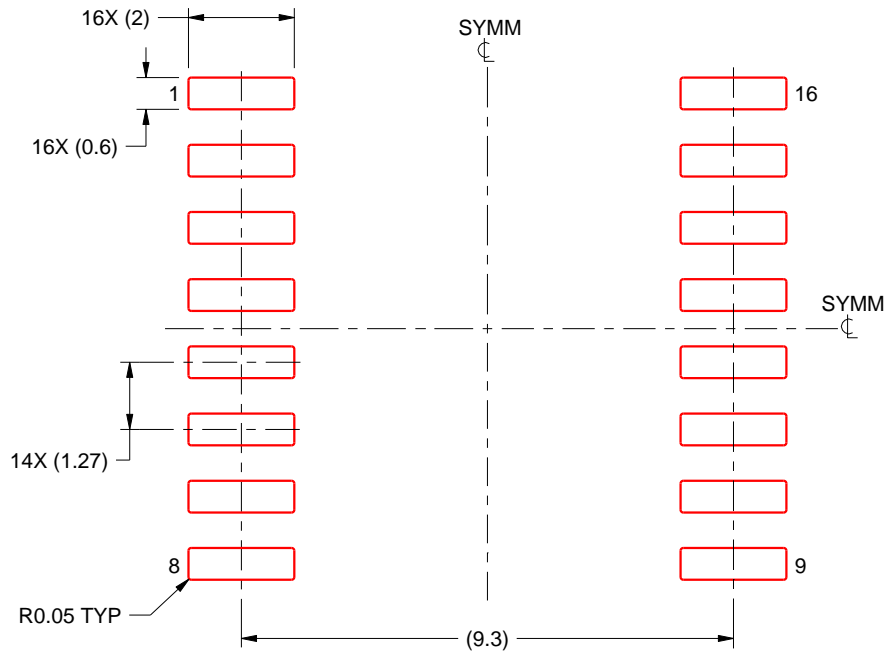
7. Solder mask tolerances between and around signal pads can vary based on board fabrication site.

EXAMPLE STENCIL DESIGN

DW0016A

SOIC - 2.65 mm max height

SOIC



SOLDER PASTE EXAMPLE
BASED ON 0.125 mm THICK STENCIL
SCALE:7X

4220721/A 07/2016

NOTES: (continued)

8. Laser cutting apertures with trapezoidal walls and rounded corners may offer better paste release. IPC-7525 may have alternate design recommendations.
9. Board assembly site may have different recommendations for stencil design.

DB (R-PDSO-G**)

PLASTIC SMALL-OUTLINE

28 PINS SHOWN



- NOTES: A. All linear dimensions are in millimeters.
 B. This drawing is subject to change without notice.
 C. Body dimensions do not include mold flash or protrusion not to exceed 0,15.
 D. Falls within JEDEC MO-150

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